Product data sheet

1. General description

The 74LVC00A provides four 2-input NAND gates.

Schmitt trigger action at all inputs makes the circuit tolerant of slower input rise and fall times.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V applications.

2. Features and benefits

- 5 V tolerant inputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 3.6 V
- CMOS low-power consumption
- Direct interface with TTL levels
- Complies with JEDEC standard:
 - ◆ JESD8-7A (1.65 V to 1.95 V)
 - ◆ JESD8-5A (2.3 V to 2.7 V)
 - JESD8-C/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-B exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

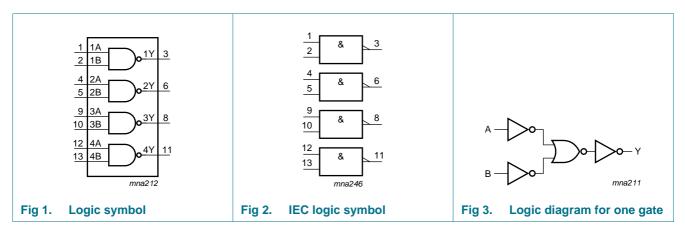
Table 1.Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74LVC00AD	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1				
74LVC00ADB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1				
74LVC00APW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1				
74LVC00ABQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1				



Quad 2-input NAND gate

4. Functional diagram



5. Pinning information

V CC terminal 1 index area 14 -J 2 (13 1B 4B 14 V_{CC} 1A 1 3) (12 4A 1Y 1B 2 13 4B 4) 00 (11 4Y 2A 1Y 3 12 4A 2A 4 00 11 4Y (10 5) 3B 2B GND⁽¹⁾ 2B 5 10 3B 6 (9 ЗA 2Y 600 2Y 6 9 3A GND 7 8 3Y GND З 001aac939 Transparent top view 001aac938 (1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND. Fig 4. Pin configuration SO14 and (T)SSOP14 Fig 5. **Pin configuration DHVQFN14**

5.1 Pinning

5.2 Pin description

Table 2. **Pin description** Symbol Pin Description 1A to 4A 1, 4, 9, 12 data input 1B to 4B 2.5.10.13 data input 1Y to 4Y 3, 6, 8,11 data output GND 7 ground (0 V) 14 supply voltage V_{CC}

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6. Functional description

Table 3.	Function selection ^[1]		
Input			Output
nA		nB	nY
L		Х	н
Х		L	Н
Н		Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	$V_{I} < 0 V$	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_{\rm O}$ > $V_{\rm CC}$ or $V_{\rm O}$ < 0 V	-	±50	mA
Vo	output voltage	output in HIGH or LOW-state	[2] -0.5	$V_{CC} + 0.5$	V
I _O	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \text{ to } +125 \ ^{\circ}C$	[3] _	500	mW
T _{stg}	storage temperature		-65	+150	°C

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] For SO14 packages: above 70 °C derate linearly with 8 mW/K.
 For (T)SSOP14 packages: above 60 °C derate linearly with 5.5 mW/K.
 For DHVQFN14 packages: above 60 °C derate linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5.	Recommended operating of	conditions				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		1.65	-	3.6	V
		functional	1.2	-	-	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	output HIGH or LOW state	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and	V_{CC} = 1.65 V to 2.7 V	0	-	20	ns/V
	fall rate	V _{CC} = 2.7 V to 3.6 V	0	-	10	ns/V

Quad 2-input NAND gate

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	–40 °C to +85 °C			–40 °C to +125 °C	
			Min	Typ[1]	Max	Min	Мах	
/ _{IH}	HIGH-level	V _{CC} = 1.2 V	1.08	-	-	1.08	-	V
	input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	$0.65 \times V_{CC}$	-	V
	V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V	
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
VIL	LOW-level	V _{CC} = 1.2 V	-	-	0.12	-	0.12	V
	input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	-	-	0.8	-	0.8	V
V _{OH} HIGH-level output voltage		$V_{I} = V_{IH} \text{ or } V_{IL}$						
		$I_{O} = -100 \ \mu A;$ $V_{CC} = 1.65 \ V \text{ to } 3.6 \ V$	$V_{CC}-0.2$	-	-	$V_{CC}-0.3$	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	1.05	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.8	-	-	1.65	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	2.05	-	V
		$I_{O} = -18$ mA; $V_{CC} = 3.0$ V	2.4	-	-	2.25	-	V
		$I_{O} = -24$ mA; $V_{CC} = 3.0$ V	2.2	-	-	2.0	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	output voltage	$I_{O} = 100 \ \mu A;$ $V_{CC} = 1.65 \ V \text{ to } 3.6 \ V$	-	-	0.2	-	0.3	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	-	0.65	V
		I_{O} = 8 mA; V_{CC} = 2.3 V	-	-	0.6	-	0.8	V
		I_{O} = 12 mA; V_{CC} = 2.7 V	-	-	0.4	-	0.6	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	0.8	V
lı	input leakage current	V_{CC} = 3.6 V; V_{I} = 5.5 V or GND	-	±0.1	±5	-	±20	μA
сс	supply current	$\label{eq:VCC} \begin{array}{l} V_{CC} = 3.6 \ \text{V}; \ \text{V}_{\text{I}} = \text{V}_{CC} \ \text{or GND}; \\ \text{I}_{O} = 0 \ \text{A} \end{array}$	-	0.1	10	-	40	μA
∆l _{CC}	additional supply current	per input pin; $V_{CC} = 2.7 V \text{ to } 3.6 V;$ $V_I = V_{CC} - 0.6 V; I_O = 0 A$	-	5	500	-	5000	μA
CI	input capacitance	$V_{CC} = 0 V$ to 3.6 V; V _I = GND to V _{CC}	-	4.0	-	-	-	pF

[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 7.

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
			-		Typ <mark>[1]</mark>	Max	Min	Max	
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	[2]						
	V _{CC} = 1.2 V		-	12	-	-	-	ns	
		V_{CC} = 1.65 V to 1.95 V		0.3	3.8	8.4	0.3	9.7	ns
	V_{CC} = 2.3 V to 2.7 V		1.0	2.2	4.8	1.0	5.7	ns	
	$V_{CC} = 2.7 V$		1.0	2.3	5.1	1.0	5.9	ns	
		V_{CC} = 3.0 V to 3.6 V		0.5	2.0	4.3	0.5	5.1	ns
t _{sk(o)}	output skew time	V_{CC} = 3.0 V to 3.6 V	[3]	-	-	1.0	-	1.5	ns
C _{PD}	power dissipation	per gate; V_I = GND to V_{CC}	[4]						
	capacitance	V_{CC} = 1.65 V to 1.95 V		-	5.6	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	8.9	-	-	-	pF
		V_{CC} = 3.0 V to 3.6 V		-	11.8	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.2 V, 1.8 V, 2.5 V, 2.7 V, and 3.3 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz; f_o = output frequency in MHz

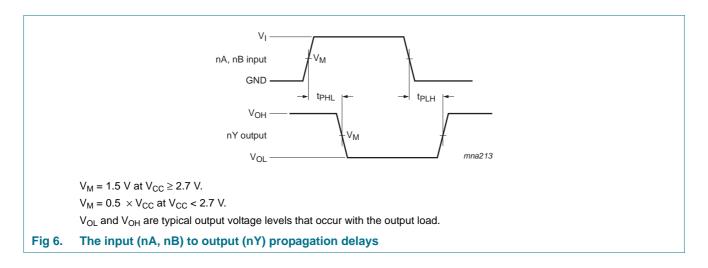
 C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

N = number of inputs switching

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs

11. Waveforms



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74LVC00A

Quad 2-input NAND gate

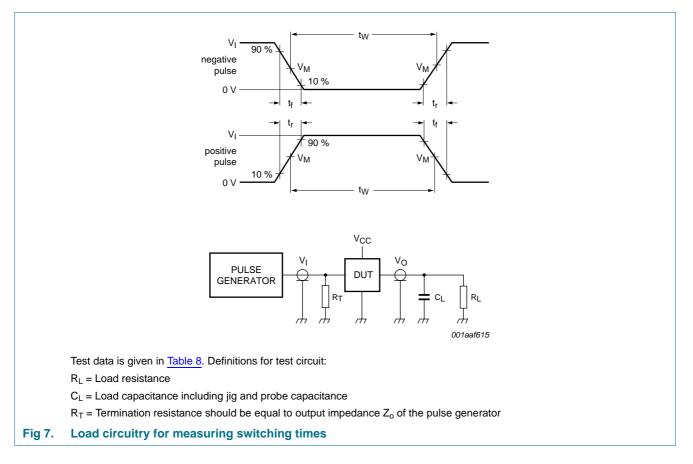


Table 8. Test data

Supply voltage	Input		Load	Load		
	VI	t _r , t _f	CL	RL		
1.2 V	V _{CC}	≤ 2 ns	30 pF	1 kΩ		
1.65 V to 1.95 V	V _{CC}	≤2 ns	30 pF	1 kΩ		
2.3 V to 2.7 V	V _{CC}	≤2 ns	30 pF	500 Ω		
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω		
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω		

Quad 2-input NAND gate

12. Package outline

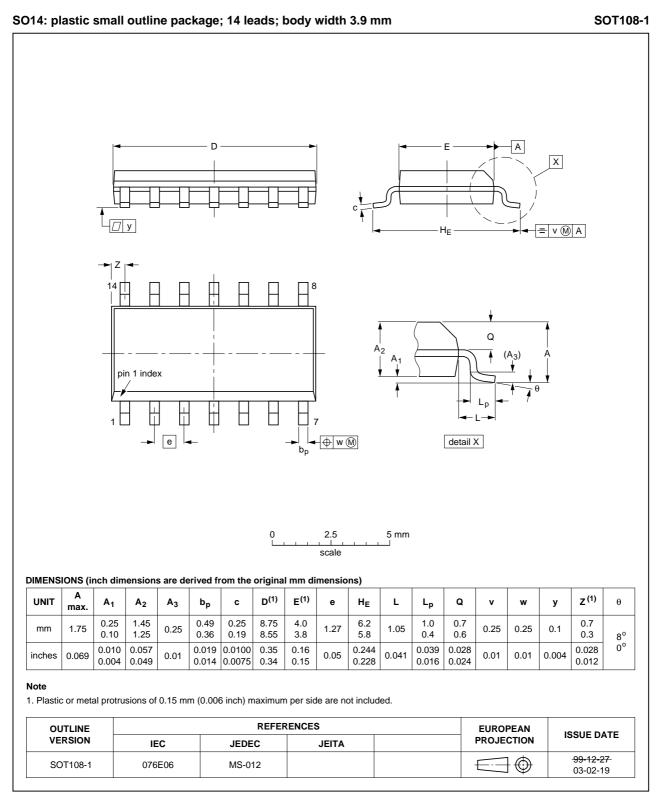


Fig 8. Package outline SOT108-1 (SO14)

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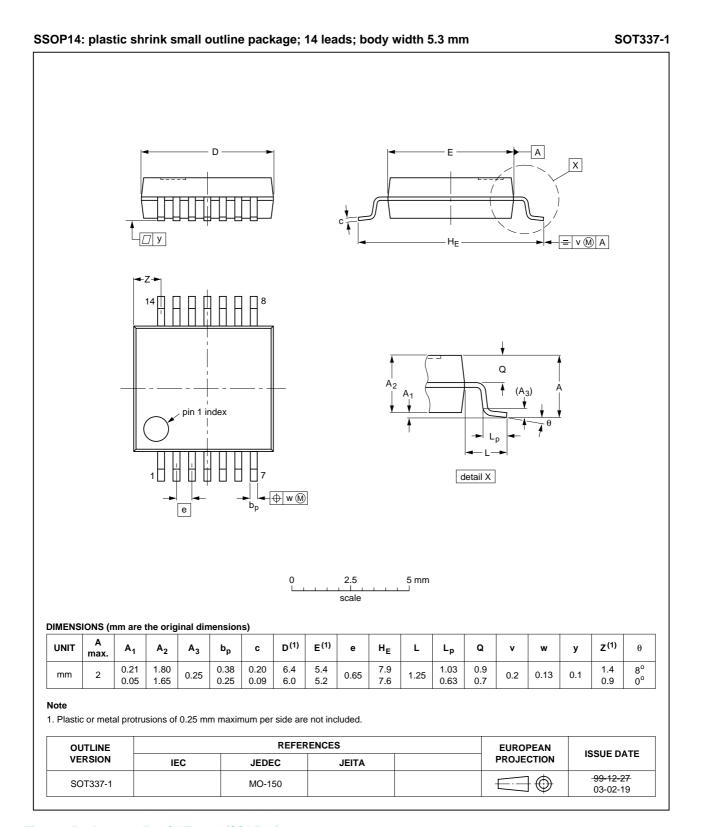


Fig 9. Package outline SOT337-1 (SSOP14)

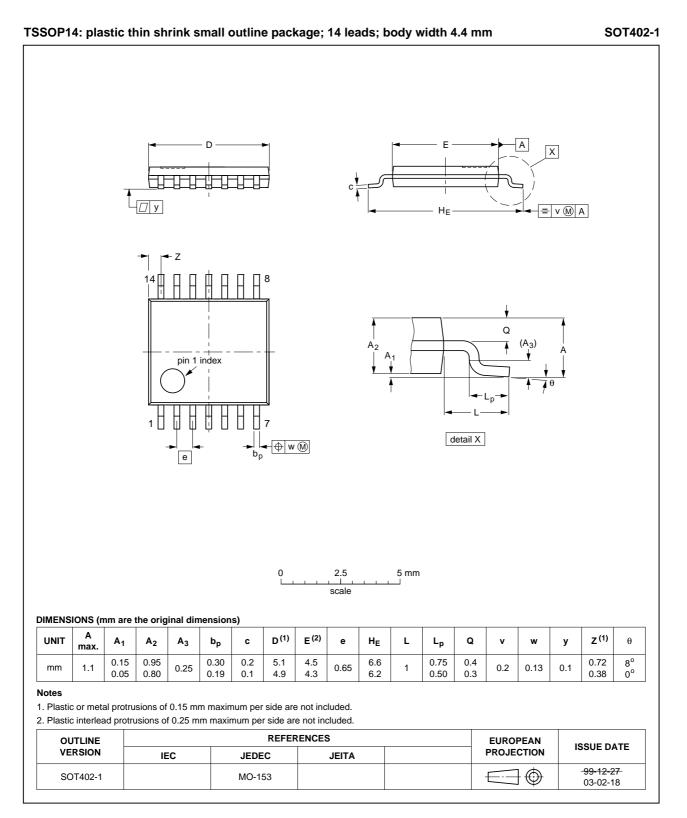
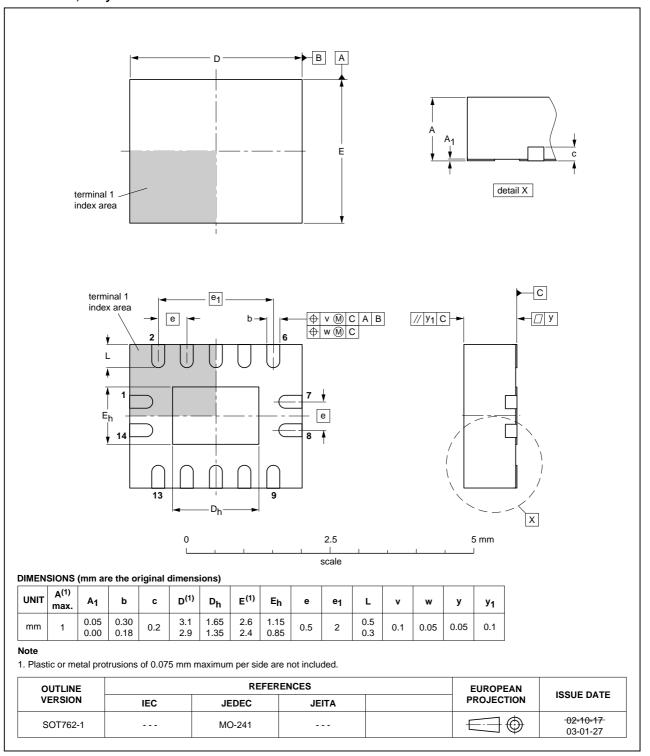


Fig 10. Package outline SOT402-1 (TSSOP14)

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

Fig 11. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 9.	Abbreviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 10. Revision history

	· · · · · · · · · · · · · · · · · · ·			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC00A v.7	20120425	Product data sheet	-	74LVC00A v.6
Modifications:	• <u>Table 2</u> : Errata	in pin description corrected		
74LVC00A v.6	20120106	Product data sheet	-	74LVC00A v.5
Modifications:	 The format of t of NXP Semice 		lesigned to comply wit	h the new identity guidelines
	 Legal texts have 	ve been adapted to the new	company name where	e appropriate.
	• Table 4, Table	5, <u>Table 6, Table 7</u> and <u>Tabl</u>	<u>e 8</u> : values added for I	ower voltage ranges.
74LVC00A v.5	20030904	Product specification	-	74LVC00A v.4
74LVC00A v.4	20030507	Product specification	-	74LVC00A v.3
74LVC00A v.3	20020305	Product specification	-	74LVC00A v.2
74LVC00A v.2	19980428	Product specification	-	74LVC00A v.1
74LVC00A v.1	19970811	Product specification	-	-

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Quad 2-input NAND gate

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